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[Embedded - System On Chip \(SoC\)](#): The Heart of Modern Embedded Systems

[Embedded - System On Chip \(SoC\)](#) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are [Embedded - System On Chip \(SoC\)](#)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM® Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 103K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BFBGA, FCBGA
Supplier Device Package	484-FCBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu2cg-2sbva484i

Available Speed Grades and Operating Voltages

Table 3 describes the speed grades per device and the V_{CCINT} operating supply voltages for the full-power, low-power, and DDR domains. For more information on selecting devices and speed grades, see the *UltraScale Architecture and Product Overview* ([DS890](#)).

Table 3: Available Speed Grades and Operating Voltages

Speed Grade	V_{CCINT}	$V_{CC_PSINTLP}$	$V_{CC_PSINTFP}$	$V_{CC_PSINTFP_DDR}$	Units
-3E	0.90	0.90	0.90	0.90	V
-2E	0.85	0.85	0.85	0.85	V
-2I	0.85	0.85	0.85	0.85	V
-2LE	0.85	0.85	0.85	0.85	V
-1E	0.85	0.85	0.85	0.85	V
-1I	0.85	0.85	0.85	0.85	V
-1LI	0.85	0.85	0.85	0.85	V
-2LE	0.72	0.85	0.85	0.85	V
-1LI	0.72	0.85	0.85	0.85	V

DC Characteristics Over Recommended Operating Conditions

Table 4: DC Characteristics Over Recommended Operating Conditions

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.68	—	—	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	—	—	V
I_{REF}	V_{REF} leakage current per pin.	—	—	15	μA
I_L	Input or output leakage current per pin (sample-tested). ⁽²⁾	—	—	15	μA
$C_{IN}^{(3)}$	Die input capacitance at the pad (HP I/O).	—	—	3.1	pF
	Die input capacitance at the pad (HD I/O).	—	—	4.75	pF
I_{RPU}	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO} = 3.3V$.	75	—	190	μA
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO} = 2.5V$.	50	—	169	μA
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO} = 1.8V$.	60	—	120	μA
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO} = 1.5V$.	30	—	120	μA
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO} = 1.2V$.	10	—	100	μA
I_{RPD}	Pad pull-down (when selected) at $V_{IN} = 3.3V$.	60	—	200	μA
	Pad pull-down (when selected) at $V_{IN} = 1.8V$.	29	—	120	μA
$I_{CCADCONPL}$	Analog supply current for the PL SYSMON circuits in the power-up state.	—	—	8	mA
$I_{CCADCONPS}$	Analog supply current for the PS SYSMON circuits in the power-up state.	—	—	10	mA
$I_{CCADCOFFPL}$	Analog supply current for the PL SYSMON circuits in the power-down state.	—	—	1.5	mA
$I_{CCADCOFFPS}$	Analog supply current for the PS SYSMON circuits in the power-down state.	—	—	1.8	mA

Table 4: DC Characteristics Over Recommended Operating Conditions (Cont'd)

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
$I_{CC_PSBATT}^{(4)(5)}$	Battery supply current at $V_{CC_PSBATT} = 1.50V$, RTC enabled.	–	–	3650	nA
	Battery supply current at $V_{CC_PSBATT} = 1.50V$, RTC disabled.	–	–	650	nA
	Battery supply current at $V_{CC_PSBATT} = 1.20V$, RTC enabled.	–	–	3150	nA
	Battery supply current at $V_{CC_PSBATT} = 1.20V$, RTC disabled.	–	–	150	nA
$I_{PSFS}^{(6)}$	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks ⁽⁸⁾ (measured per JEDEC specification)					
$R^{(9)}$	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–10% ⁽⁷⁾	40	+10% ⁽⁷⁾	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–10% ⁽⁷⁾	48	+10% ⁽⁷⁾	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–10% ⁽⁷⁾	60	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10% ⁽⁷⁾	40	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10% ⁽⁷⁾	48	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10% ⁽⁷⁾	60	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10% ⁽⁷⁾	120	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10% ⁽⁷⁾	240	+10% ⁽⁷⁾	Ω
Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)					
$R^{(9)}$	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)					
$R^{(9)}$	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	$V_{CCO} \times 0.49$	$V_{CCO} \times 0.50$	$V_{CCO} \times 0.51$	V
	70% V_{CCO}	$V_{CCO} \times 0.69$	$V_{CCO} \times 0.70$	$V_{CCO} \times 0.71$	V

Quiescent Supply Current

Table 9: Typical Quiescent Supply Current⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units		
			0.90V		0.85V		0.72V			
			-3	-2	-1	-2	-1			
I _{CCINTQ}	Quiescent V _{CCINT} supply current.	XCZU2	N/A	393	393	344	344	mA		
		XCZU3	N/A	393	393	344	344	mA		
		XCZU4	719	684	684	601	601	mA		
		XCZU5	719	684	684	601	601	mA		
		XCZU6	1629	1549	1549	1358	1358	mA		
		XCZU7	1263	1201	1201	1055	1055	mA		
		XCZU9	1629	1549	1549	1358	1358	mA		
		XCZU11	1786	1699	1699	1491	1491	mA		
		XCZU15	1987	1890	1890	1660	1660	mA		
		XCZU17	2728	2594	2594	2275	2275	mA		
I _{CCINT_IOQ}	Quiescent V _{CCINT_IO} supply current.	XCZU19	2728	2594	2594	2275	2275	mA		
		XCZU2	N/A	44	44	44	44	mA		
		XCZU3	N/A	44	44	44	44	mA		
		XCZU4	61	59	59	59	59	mA		
		XCZU5	61	59	59	59	59	mA		
		XCZU6	61	59	59	59	59	mA		
		XCZU7	120	115	115	115	115	mA		
		XCZU9	61	59	59	59	59	mA		
		XCZU11	120	115	115	115	115	mA		
		XCZU15	61	59	59	59	59	mA		
I _{CCOQ}	Quiescent V _{CCO} supply current.	XCZU17	164	158	158	158	158	mA		
		XCZU19	164	158	158	158	158	mA		
I _{CCAUXQ}	Quiescent V _{CCAUX} supply current.	All devices	1	1	1	1	1	mA		
		XCZU2	N/A	55	55	55	55	mA		
		XCZU3	N/A	55	55	55	55	mA		
		XCZU4	90	90	90	90	90	mA		
		XCZU5	90	90	90	90	90	mA		
		XCZU6	227	227	227	227	227	mA		
		XCZU7	174	174	174	174	174	mA		
		XCZU9	227	227	227	227	227	mA		
		XCZU11	255	255	255	255	255	mA		
		XCZU15	266	266	266	266	266	mA		
		XCZU17	396	396	396	396	396	mA		
		XCZU19	396	396	396	396	396	mA		

Table 19: Complementary Differential SelectIO DC Input and Output Levels for HP I/O Banks⁽¹⁾

I/O Standard	V _{ICM} (V) ⁽²⁾			V _{ID} (V) ⁽³⁾		V _{OL} (V) ⁽⁴⁾	V _{OH} (V) ⁽⁵⁾	I _{OL}	I _{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.680	V _{CCO} /2	(V _{CCO} /2) + 0.150	0.100	–	0.400	V _{CCO} – 0.400	5.8	-5.8
DIFF_HSTL_I_12	0.400 × V _{CCO}	V _{CCO} /2	0.600 × V _{CCO}	0.100	–	0.250 × V _{CCO}	0.750 × V _{CCO}	4.1	-4.1
DIFF_HSTL_I_18	(V _{CCO} /2) – 0.175	V _{CCO} /2	(V _{CCO} /2) + 0.175	0.100	–	0.400	V _{CCO} – 0.400	6.2	-6.2
DIFF_HSUL_12	(V _{CCO} /2) – 0.120	V _{CCO} /2	(V _{CCO} /2) + 0.120	0.100	–	20% V _{CCO}	80% V _{CCO}	0.1	-0.1
DIFF_SSTL12	(V _{CCO} /2) – 0.150	V _{CCO} /2	(V _{CCO} /2) + 0.150	0.100	–	(V _{CCO} /2) – 0.150	(V _{CCO} /2) + 0.150	8.0	-8.0
DIFF_SSTL135	(V _{CCO} /2) – 0.150	V _{CCO} /2	(V _{CCO} /2) + 0.150	0.100	–	(V _{CCO} /2) – 0.150	(V _{CCO} /2) + 0.150	9.0	-9.0
DIFF_SSTL15	(V _{CCO} /2) – 0.175	V _{CCO} /2	(V _{CCO} /2) + 0.175	0.100	–	(V _{CCO} /2) – 0.175	(V _{CCO} /2) + 0.175	10.0	-10.0
DIFF_SSTL18_I	(V _{CCO} /2) – 0.175	V _{CCO} /2	(V _{CCO} /2) + 0.175	0.100	–	(V _{CCO} /2) – 0.470	(V _{CCO} /2) + 0.470	7.0	-7.0

Notes:

1. DIFF POD10 and DIFF POD12 HP I/O bank specifications are shown in Table 20, Table 21, and Table 22.
2. V_{ICM} is the input common mode voltage.
3. V_{ID} is the input differential voltage.
4. V_{OL} is the single-ended low-output voltage.
5. V_{OH} is the single-ended high-output voltage.

Table 20: DC Input Levels for Differential POD10 and POD12 I/O Standards⁽¹⁾⁽²⁾

I/O Standard	V _{ICM} (V)			V _{ID} (V)	
	Min	Typ	Max	Min	Max
DIFF_POD10	0.63	0.70	0.77	0.14	–
DIFF_POD12	0.76	0.84	0.92	0.16	–

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* ([UG571](#)).

Table 21: DC Output Levels for Single-ended and Differential POD10 and POD12 Standards⁽¹⁾⁽²⁾

Symbol	Description	V _{OUT}	Min	Typ	Max	Units
R _{OL}	Pull-down resistance.	V _{OM_DC} (as described in Table 22)	36	40	44	Ω
R _{OH}	Pull-up resistance.	V _{OM_DC} (as described in Table 22)	36	40	44	Ω

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* ([UG571](#)).

Table 22: Table 21 Definitions for DC Output Levels for POD Standards

Symbol	Description	All Speed Grades	Units
V _{OM_DC}	DC output Mid measurement level (for IV curve linearity).	0.8 × V _{CCO}	V

Table 26: Speed Grade Designations by Device (Cont'd)

Device	Speed Grade, Temperature Ranges, and V _{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU5EG	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU5EV	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU6CG	-2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)
XCZU6EG	-3E (V _{CCINT} = 0.90V) -2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)
XCZU7CG	-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU7EG	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU7EV	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU9CG	-2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)
XCZU9EG	-3E (V _{CCINT} = 0.90V) -2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)

Table 26: Speed Grade Designations by Device (Cont'd)

Device	Speed Grade, Temperature Ranges, and V _{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU11EG	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU15EG	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU17EG	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU19EG	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		

Notes:

1. The lowest power -1L and -2L devices, where V_{CCINT} = 0.72V, are listed in the Vivado Design Suite as -1LV and -2LV respectively.

Table 37: PS Reset Assertion Timing Requirements

Symbol	Description	Min	Typ	Max	Units
T _{PSPOR}	Required PS_POR_B assertion time. ⁽¹⁾	10	—	—	μs
T _{PSRST}	Required PS_SRST_B assertion time.	3	—	—	PS_REF_CLK Clock Cycles

Notes:

1. PS_POR_B must be asserted Low at power-up and continue to be asserted for a duration of T_{PSPOR} after all the PS supply voltages reach minimum levels. PS_POR_B must be asserted Low for the duration of T_{POR} when the PS and PL power-up at the same time and the application uses both the PS and PL after power-up.

Table 38: PS Clocks Switching Characteristics

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F _{TOPSW_MAINMAX}	TOPSW_MAIN maximum frequency.	600	533	533	MHz
F _{TOPSW_LSBUSMAX}	TOPSW_LSBUS maximum frequency.	100	100	100	MHz
F _{GDMAMAX}	FPD-DMA maximum frequency.	600	600	600	MHz
F _{DPDMAMAX}	DisplayPort DMA maximum frequency.	600	600	600	MHz
F _{LPD_SWITCH_CTRLMAX}	LPD_SWITCH_CTRL maximum frequency.	600	500	500	MHz
F _{LPD_LSBUS_CTRLMAX}	LPD_LSBUS_CTRL maximum frequency.	100	100	100	MHz
F _{ADMAMAX}	LPD-DMA maximum frequency.	600	500	500	MHz
F _{APLL_TO_LPDMAX}	APLL_TO_LPD maximum frequency.	533	533	533	MHz
F _{DPLL_TO_LPDMAX}	DPLL_TO_LPD maximum frequency.	533	533	533	MHz
F _{VPLL_TO_LPDMAX}	VPLL_TO_LPD maximum frequency.	533	533	533	MHz
F _{IOPLLU_TO_LPDMAX}	IOPLLU_TO_LPD maximum frequency.	533	533	533	MHz
F _{RPLL_TO_FPDMAX}	RPLL_TO_FPD maximum frequency.	533	533	533	MHz

PS Configuration

Table 39: Processor Configuration Access Port Switching Characteristics

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units	
		0.90V	0.85V	0.72V				
		-3	-2	-1	-2	-1		
F _{PCAPCK}	Maximum processor configuration access port (PCAP) frequency.	200	200	200	150	150	MHz	

Table 40: Boundary-Scan Port Switching Characteristics

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units	
		0.90V	0.85V	0.72V				
		-3	-2	-1	-2	-1		
F _{TCK}	JTAG clock maximum frequency.	25	25	25	15	15	MHz	
T _{TAPTCK/TCKTAP}	TMS and TDI setup and hold.	4.0/2.0	4.0/2.0	4.0/2.0	5.0/2.0	5.0/2.0	ns, Min	
T _{TCKTDO}	TCK falling edge to TDO output.	16.1	16.1	16.1	24	24	ns, Max	

Notes:

1. The test conditions are configured to the LVC MOS 3.3V I/O standard with a 12 mA drive strength.

PS Gigabit Ethernet Controller Interface

Table 44: RGMII Interface⁽¹⁾

Symbol	Description	Min	Max	Units
T _{DGEMTXCLK}	Transmit clock duty cycle.	45	55	%
T _{GEMTXCKO}	TXD output clock to out time.	-0.5	0.5	ns
T _{GEMRXDCK}	RXD input setup time.	0.8	—	ns
T _{GEMRXCKD}	RXD input hold time.	0.8	—	ns
T _{MdioCLK}	MDC output clock period.	400	—	ns
T _{MdioCKL}	MDC low time.	160	—	ns
T _{MdioCKH}	MDC high time.	160	—	ns
T _{MdiODCK}	MDIO input data setup time.	80	—	ns
T _{MdiOCKD}	MDIO input data hold time.	0.0	—	ns
T _{MdiOCKO}	MDIO output data delay time.	-1.0	15	ns
F _{GETXCLK}	RGMII_TX_CLK transmit clock frequency.	—	125	MHz
F _{GERXCLK}	RGMII_RX_CLK receive clock frequency.	—	125	MHz
F _{ENET_REF_CLK}	Ethernet reference clock frequency.	—	125	MHz

Notes:

1. The test conditions are configured to the LVCMS 2.5V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS SD/SDIO Controller Interface

Table 45: SD/SDIO Interface⁽¹⁾

Symbol	Description	Min	Max	Units
SD/SDIO Interface DDR50 Mode				
T _{DCDDRCLK}	SD device clock duty cycle.	45	55	%
T _{SDDDRCK01}	Clock to output delay, data. ⁽²⁾	1.0	6.8	ns
T _{SDDRIVW}	Input valid data window. ⁽³⁾	3.5	—	ns
T _{SDDDRDCK2}	Input setup time, command.	4.7	—	ns
T _{SDDDRCKD2}	Input hold time, command.	1.5	—	ns
T _{SDDDRCK02}	Clock to output delay, command.	1.0	13.8	ns
F _{SDDDRCLK}	High-speed mode SD device clock frequency.	—	50	MHz
SD/SDIO Interface SDR104				
T _{DCSDHSCLK1}	SD device clock duty cycle.	40	60	%
T _{SdSDRCK01}	Clock to output delay, all outputs. ⁽²⁾	1.0	3.2	ns
T _{SdSDR1IVW}	Input valid data window. ⁽³⁾	0.5	—	UI
F _{SdSDRCLK1}	SDR104 mode device clock frequency.	—	200	MHz
SD/SDIO Interface SDR50/25				
T _{DCSDHSCLK2}	SD device clock duty cycle.	40	60	%
T _{SdSDRCK02}	Clock to output delay, all outputs. ⁽²⁾	1.0	6.8	ns
T _{SdSDR2IVW}	Input valid data window. ⁽³⁾	0.3	—	UI

PS DAP Interface

Table 50: DAP Interface⁽¹⁾

Symbol	Description ⁽²⁾	Min	Max	Units
T _{PDAPDCK}	PS DAP input setup time.	3.0	–	ns
T _{PDAPCKD}	PS DAP input hold time.	2.0	–	ns
T _{PDAPCKO}	PS DAP clock to out delay.	–	10.86	ns
T _{PDAPCLK}	PS DAP clock frequency.	–	44	MHz

Notes:

1. The test conditions are configured to the LVC MOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.
2. PS DAP interface signals connect to MIO pins.

PS UART Interface

Table 51: UART Interface⁽¹⁾

Symbol	Description	Min	Max	Units
BAUD _{TXMAX}	Transmit baud rate.	–	6.25	Mb/s
BAUD _{RXMAX}	Receive baud rate.	–	6.25	Mb/s
F _{UART_REF_CLK}	UART reference clock frequency.	–	100	MHz

Notes:

1. The test conditions are configured to the LVC MOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS General Purpose I/O Interface

Table 52: General Purpose I/O (GPIO) Interface

Symbol	Description	Min	Max	Units
T _{PWGPIOH}	Input High pulse width.	10 x 1/F _{LPD_LSBUS_CTRLMAX}	–	μs
T _{PWGPIOL}	Input Low pulse width.	10 x 1/F _{LPD_LSBUS_CTRLMAX}	–	μs

PS Trace Interface

Table 53: Trace Interface⁽¹⁾

Symbol	Description	Min	Max	Units
T _{TCECKO}	Trace clock to output delay, all outputs.	–0.5	0.5	ns
T _{DCTCECLK}	Trace clock duty cycle.	45	55	%
F _{TCECLK}	Trace clock frequency.	–	125	MHz

Notes:

1. The test conditions are configured to the LVC MOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

Table 75: IOB High Density (HD) Switching Characteristics (Cont'd)

I/O Standards	T _{INBUF_DELAY_PAD_I}					T _{OUTBUF_DELAY_O_PAD}					T _{OUTBUF_DELAY_TD_PAD}					Units
	0.90V		0.85V		0.72V	0.90V		0.85V		0.72V	0.90V		0.85V		0.72V	
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
HSTL_I_F	0.856	0.856	0.900	0.856	0.900	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
HSTL_I_S	0.856	0.856	0.900	0.856	0.900	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
HSUL_12_F	0.780	0.780	0.867	0.780	0.867	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
HSUL_12_S	0.780	0.780	0.867	0.780	0.867	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
LVCMOS12_F_12	0.918	0.918	0.976	0.918	0.976	1.689	1.689	1.856	1.689	1.856	1.202	1.202	1.317	1.202	1.317	ns
LVCMOS12_F_4	0.918	0.918	0.976	0.918	0.976	1.742	1.742	1.922	1.742	1.922	1.353	1.353	1.478	1.353	1.478	ns
LVCMOS12_F_8	0.918	0.918	0.976	0.918	0.976	1.714	1.714	1.879	1.714	1.879	1.292	1.292	1.432	1.292	1.432	ns
LVCMOS12_S_12	0.918	0.918	0.976	0.918	0.976	2.073	2.073	2.247	2.073	2.247	1.581	1.581	1.717	1.581	1.717	ns
LVCMOS12_S_4	0.918	0.918	0.976	0.918	0.976	1.979	1.979	2.182	1.979	2.182	1.633	1.633	1.772	1.633	1.772	ns
LVCMOS12_S_8	0.918	0.918	0.976	0.918	0.976	2.205	2.205	2.406	2.205	2.406	1.767	1.767	1.928	1.767	1.928	ns
LVCMOS15_F_12	0.905	0.905	0.958	0.905	0.958	1.713	1.713	1.892	1.713	1.892	1.275	1.275	1.428	1.275	1.428	ns
LVCMOS15_F_16	0.905	0.905	0.958	0.905	0.958	1.722	1.722	1.881	1.722	1.881	1.260	1.260	1.407	1.260	1.407	ns
LVCMOS15_F_4	0.905	0.905	0.958	0.905	0.958	1.825	1.825	1.959	1.825	1.959	1.453	1.453	1.557	1.453	1.557	ns
LVCMOS15_F_8	0.905	0.905	0.958	0.905	0.958	1.778	1.778	1.930	1.778	1.930	1.378	1.378	1.458	1.378	1.458	ns
LVCMOS15_S_12	0.905	0.905	0.958	0.905	0.958	1.991	1.991	2.139	1.991	2.139	1.516	1.516	1.648	1.516	1.648	ns
LVCMOS15_S_16	0.905	0.905	0.958	0.905	0.958	2.172	2.172	2.389	2.172	2.389	1.707	1.707	1.888	1.707	1.888	ns
LVCMOS15_S_4	0.905	0.905	0.958	0.905	0.958	2.313	2.313	2.483	2.313	2.483	1.952	1.952	2.123	1.952	2.123	ns
LVCMOS15_S_8	0.905	0.905	0.958	0.905	0.958	2.170	2.170	2.400	2.170	2.400	1.817	1.817	1.984	1.817	1.984	ns
LVCMOS18_F_12	0.915	0.915	0.958	0.915	0.958	1.805	1.805	1.962	1.805	1.962	1.383	1.383	1.471	1.383	1.471	ns
LVCMOS18_F_16	0.915	0.915	0.958	0.915	0.958	1.785	1.785	1.917	1.785	1.917	1.338	1.338	1.446	1.338	1.446	ns
LVCMOS18_F_4	0.915	0.915	0.958	0.915	0.958	1.868	1.868	2.013	1.868	2.013	1.472	1.472	1.599	1.472	1.599	ns
LVCMOS18_F_8	0.915	0.915	0.958	0.915	0.958	1.797	1.797	1.979	1.797	1.979	1.384	1.384	1.487	1.384	1.487	ns
LVCMOS18_S_12	0.915	0.915	0.958	0.915	0.958	2.201	2.201	2.408	2.201	2.408	1.762	1.762	1.894	1.762	1.894	ns
LVCMOS18_S_16	0.915	0.915	0.958	0.915	0.958	2.173	2.173	2.362	2.173	2.362	1.702	1.702	1.834	1.702	1.834	ns
LVCMOS18_S_4	0.915	0.915	0.958	0.915	0.958	2.346	2.346	2.567	2.346	2.567	1.951	1.951	2.092	1.951	2.092	ns
LVCMOS18_S_8	0.915	0.915	0.958	0.915	0.958	2.292	2.292	2.511	2.292	2.511	1.848	1.848	2.008	1.848	2.008	ns
LVCMOS25_F_12	0.988	0.988	1.042	0.988	1.042	2.153	2.153	2.453	2.153	2.453	1.692	1.692	1.856	1.692	1.856	ns
LVCMOS25_F_16	0.988	0.988	1.042	0.988	1.042	2.105	2.105	2.406	2.105	2.406	1.623	1.623	1.786	1.623	1.786	ns
LVCMOS25_F_4	0.988	0.988	1.042	0.988	1.042	2.344	2.344	2.554	2.344	2.554	1.842	1.842	2.039	1.842	2.039	ns
LVCMOS25_F_8	0.988	0.988	1.042	0.988	1.042	2.184	2.184	2.516	2.184	2.516	1.726	1.726	1.910	1.726	1.910	ns
LVCMOS25_S_12	0.988	0.988	1.042	0.988	1.042	2.558	2.558	2.840	2.558	2.840	1.971	1.971	2.194	1.971	2.194	ns
LVCMOS25_S_16	0.988	0.988	1.042	0.988	1.042	2.449	2.449	2.740	2.449	2.740	1.852	1.852	2.063	1.852	2.063	ns
LVCMOS25_S_4	0.988	0.988	1.042	0.988	1.042	2.770	2.770	3.066	2.770	3.066	2.224	2.224	2.458	2.224	2.458	ns
LVCMOS25_S_8	0.988	0.988	1.042	0.988	1.042	2.663	2.663	2.963	2.663	2.963	2.091	2.091	2.373	2.091	2.373	ns
LVCMOS33_F_12	1.154	1.154	1.213	1.154	1.213	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVCMOS33_F_16	1.154	1.154	1.213	1.154	1.213	2.383	2.383	2.603	2.383	2.603	1.734	1.734	1.869	1.734	1.869	ns
LVCMOS33_F_4	1.154	1.154	1.213	1.154	1.213	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVCMOS33_F_8	1.154	1.154	1.213	1.154	1.213	2.603	2.603	2.822	2.603	2.822	1.937	1.937	2.130	1.937	2.130	ns
LVCMOS33_S_12	1.154	1.154	1.213	1.154	1.213	2.705	2.705	3.047	2.705	3.047	2.049	2.049	2.318	2.049	2.318	ns
LVCMOS33_S_16	1.154	1.154	1.213	1.154	1.213	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVCMOS33_S_4	1.154	1.154	1.213	1.154	1.213	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns

IOB High Performance (HP) Switching Characteristics

Table 76: IOB High Performance (HP) Switching Characteristics

I/O Standards	T _{INBUF_DELAY_PAD_I}					T _{OUTBUF_DELAY_O_PAD}					T _{OUTBUF_DELAY_TD_PAD}					Units
	0.90V		0.85V		0.72V	0.90V		0.85V		0.72V	0.90V		0.85V		0.72V	
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_12_F	0.394	0.394	0.402	0.394	0.402	0.423	0.423	0.443	0.423	0.443	0.553	0.553	0.582	0.553	0.582	ns
DIFF_HSTL_I_12_M	0.394	0.394	0.402	0.394	0.402	0.552	0.552	0.583	0.552	0.583	0.641	0.641	0.679	0.641	0.679	ns
DIFF_HSTL_I_12_S	0.394	0.394	0.402	0.394	0.402	0.752	0.752	0.800	0.752	0.800	0.813	0.813	0.868	0.813	0.868	ns
DIFF_HSTL_I_18_F	0.319	0.319	0.339	0.319	0.339	0.456	0.456	0.474	0.456	0.474	0.576	0.576	0.606	0.576	0.606	ns
DIFF_HSTL_I_18_M	0.319	0.319	0.339	0.319	0.339	0.570	0.570	0.603	0.570	0.603	0.653	0.653	0.692	0.653	0.692	ns
DIFF_HSTL_I_18_S	0.319	0.319	0.339	0.319	0.339	0.782	0.782	0.834	0.782	0.834	0.816	0.816	0.871	0.816	0.871	ns
DIFF_HSTL_I_DCI_12_F	0.394	0.394	0.402	0.394	0.402	0.406	0.406	0.429	0.406	0.429	0.534	0.534	0.564	0.534	0.564	ns
DIFF_HSTL_I_DCI_12_M	0.394	0.394	0.402	0.394	0.402	0.557	0.557	0.587	0.557	0.587	0.653	0.653	0.694	0.653	0.694	ns
DIFF_HSTL_I_DCI_12_S	0.394	0.394	0.402	0.394	0.402	0.755	0.755	0.806	0.755	0.806	0.842	0.842	0.907	0.842	0.907	ns
DIFF_HSTL_I_DCI_18_F	0.323	0.323	0.339	0.323	0.339	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
DIFF_HSTL_I_DCI_18_M	0.323	0.323	0.339	0.323	0.339	0.555	0.555	0.586	0.555	0.586	0.643	0.643	0.684	0.643	0.684	ns
DIFF_HSTL_I_DCI_18_S	0.323	0.323	0.339	0.323	0.339	0.762	0.762	0.818	0.762	0.818	0.836	0.836	0.900	0.836	0.900	ns
DIFF_HSTL_I_DCI_F	0.397	0.397	0.417	0.397	0.417	0.431	0.431	0.445	0.431	0.445	0.555	0.555	0.575	0.555	0.575	ns
DIFF_HSTL_I_DCI_M	0.397	0.397	0.417	0.397	0.417	0.553	0.553	0.583	0.553	0.583	0.644	0.644	0.684	0.644	0.684	ns
DIFF_HSTL_I_DCI_S	0.397	0.397	0.417	0.397	0.417	0.767	0.767	0.823	0.767	0.823	0.848	0.848	0.912	0.848	0.912	ns
DIFF_HSTL_I_F	0.404	0.404	0.417	0.404	0.417	0.423	0.423	0.443	0.423	0.443	0.549	0.549	0.581	0.549	0.581	ns
DIFF_HSTL_I_M	0.404	0.404	0.417	0.404	0.417	0.555	0.555	0.586	0.555	0.586	0.640	0.640	0.677	0.640	0.677	ns
DIFF_HSTL_I_S	0.404	0.404	0.417	0.404	0.417	0.767	0.767	0.818	0.767	0.818	0.811	0.811	0.866	0.811	0.866	ns
DIFF_HSUL_12_DCI_F	0.381	0.381	0.400	0.381	0.400	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_HSUL_12_DCI_M	0.381	0.381	0.400	0.381	0.400	0.557	0.557	0.587	0.557	0.587	0.653	0.653	0.694	0.653	0.694	ns
DIFF_HSUL_12_DCI_S	0.381	0.381	0.400	0.381	0.400	0.737	0.737	0.787	0.737	0.787	0.822	0.822	0.885	0.822	0.885	ns
DIFF_HSUL_12_F	0.394	0.394	0.402	0.394	0.402	0.412	0.412	0.430	0.412	0.430	0.538	0.538	0.566	0.538	0.566	ns
DIFF_HSUL_12_M	0.394	0.394	0.402	0.394	0.402	0.552	0.552	0.583	0.552	0.583	0.641	0.641	0.679	0.641	0.679	ns
DIFF_HSUL_12_S	0.394	0.394	0.402	0.394	0.402	0.752	0.752	0.800	0.752	0.800	0.813	0.813	0.868	0.813	0.868	ns
DIFF_POD10_DCI_F	0.411	0.411	0.430	0.411	0.430	0.425	0.425	0.444	0.425	0.444	0.555	0.555	0.584	0.555	0.584	ns
DIFF_POD10_DCI_M	0.411	0.411	0.430	0.411	0.430	0.542	0.542	0.571	0.542	0.571	0.640	0.640	0.681	0.640	0.681	ns
DIFF_POD10_DCI_S	0.411	0.411	0.430	0.411	0.430	0.754	0.754	0.815	0.754	0.815	0.850	0.850	0.917	0.850	0.917	ns
DIFF_POD10_F	0.411	0.411	0.433	0.411	0.433	0.438	0.438	0.459	0.438	0.459	0.569	0.569	0.601	0.569	0.601	ns
DIFF_POD10_M	0.411	0.411	0.433	0.411	0.433	0.538	0.538	0.568	0.538	0.568	0.630	0.630	0.667	0.630	0.667	ns
DIFF_POD10_S	0.411	0.411	0.433	0.411	0.433	0.766	0.766	0.821	0.766	0.821	0.836	0.836	0.894	0.836	0.894	ns
DIFF_POD12_DCI_F	0.407	0.407	0.432	0.407	0.432	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_POD12_DCI_M	0.407	0.407	0.432	0.407	0.432	0.543	0.543	0.572	0.543	0.572	0.638	0.638	0.678	0.638	0.678	ns
DIFF_POD12_DCI_S	0.407	0.407	0.432	0.407	0.432	0.772	0.772	0.822	0.772	0.822	0.862	0.862	0.929	0.862	0.929	ns
DIFF_POD12_F	0.409	0.409	0.430	0.409	0.430	0.455	0.455	0.476	0.455	0.476	0.595	0.595	0.626	0.595	0.626	ns
DIFF_POD12_M	0.409	0.409	0.430	0.409	0.430	0.551	0.551	0.582	0.551	0.582	0.641	0.641	0.679	0.641	0.679	ns
DIFF_POD12_S	0.409	0.409	0.430	0.409	0.430	0.767	0.767	0.817	0.767	0.817	0.832	0.832	0.889	0.832	0.889	ns
DIFF_SSTL12_DCI_F	0.381	0.381	0.400	0.381	0.400	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_SSTL12_DCI_M	0.381	0.381	0.400	0.381	0.400	0.557	0.557	0.587	0.557	0.587	0.654	0.654	0.694	0.654	0.694	ns
DIFF_SSTL12_DCI_S	0.381	0.381	0.400	0.381	0.400	0.754	0.754	0.803	0.754	0.803	0.842	0.842	0.908	0.842	0.908	ns

Table 76: IOB High Performance (HP) Switching Characteristics (Cont'd)

I/O Standards	T _{INBUF_DELAY_PAD_I}					T _{OUTBUF_DELAY_O_PAD}					T _{OUTBUF_DELAY_TD_PAD}					Units
	0.90V		0.85V		0.72V	0.90V		0.85V		0.72V	0.90V		0.85V		0.72V	
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
SSTL135_DCI_S	0.366	0.366	0.399	0.366	0.399	0.746	0.746	0.799	0.746	0.799	0.829	0.829	0.893	0.829	0.893	ns
SSTL135_F	0.378	0.378	0.399	0.378	0.399	0.408	0.408	0.428	0.408	0.428	0.528	0.528	0.561	0.528	0.561	ns
SSTL135_M	0.378	0.378	0.399	0.378	0.399	0.555	0.555	0.585	0.555	0.585	0.641	0.641	0.679	0.641	0.679	ns
SSTL135_S	0.378	0.378	0.399	0.378	0.399	0.772	0.772	0.823	0.772	0.823	0.827	0.827	0.878	0.827	0.878	ns
SSTL15_DCI_F	0.402	0.402	0.417	0.402	0.417	0.412	0.412	0.429	0.412	0.429	0.531	0.531	0.563	0.531	0.563	ns
SSTL15_DCI_M	0.402	0.402	0.417	0.402	0.417	0.553	0.553	0.583	0.553	0.583	0.645	0.645	0.685	0.645	0.685	ns
SSTL15_DCI_S	0.402	0.402	0.417	0.402	0.417	0.768	0.768	0.822	0.768	0.822	0.847	0.847	0.912	0.847	0.912	ns
SSTL15_F	0.371	0.371	0.400	0.371	0.400	0.408	0.408	0.428	0.408	0.428	0.530	0.530	0.556	0.530	0.556	ns
SSTL15_M	0.371	0.371	0.400	0.371	0.400	0.554	0.554	0.585	0.554	0.585	0.639	0.639	0.677	0.639	0.677	ns
SSTL15_S	0.371	0.371	0.400	0.371	0.400	0.767	0.767	0.817	0.767	0.817	0.813	0.813	0.867	0.813	0.867	ns
SSTL18_I_DCI_F	0.329	0.329	0.336	0.329	0.336	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
SSTL18_I_DCI_M	0.329	0.329	0.336	0.329	0.336	0.554	0.554	0.585	0.554	0.585	0.644	0.644	0.683	0.644	0.683	ns
SSTL18_I_DCI_S	0.329	0.329	0.336	0.329	0.336	0.762	0.762	0.818	0.762	0.818	0.837	0.837	0.899	0.837	0.899	ns
SSTL18_I_F	0.316	0.316	0.337	0.316	0.337	0.454	0.454	0.476	0.454	0.476	0.578	0.578	0.608	0.578	0.608	ns
SSTL18_I_M	0.316	0.316	0.337	0.316	0.337	0.571	0.571	0.603	0.571	0.603	0.652	0.652	0.692	0.652	0.692	ns
SSTL18_I_S	0.316	0.316	0.337	0.316	0.337	0.782	0.782	0.835	0.782	0.835	0.816	0.816	0.870	0.816	0.870	ns
SUB_LVDS	0.539	0.539	0.620	0.539	0.620	0.660	0.660	0.692	0.660	0.692	969.863	969.863	969.863	969.863	969.863	ns

IOB 3-state Output Switching Characteristics

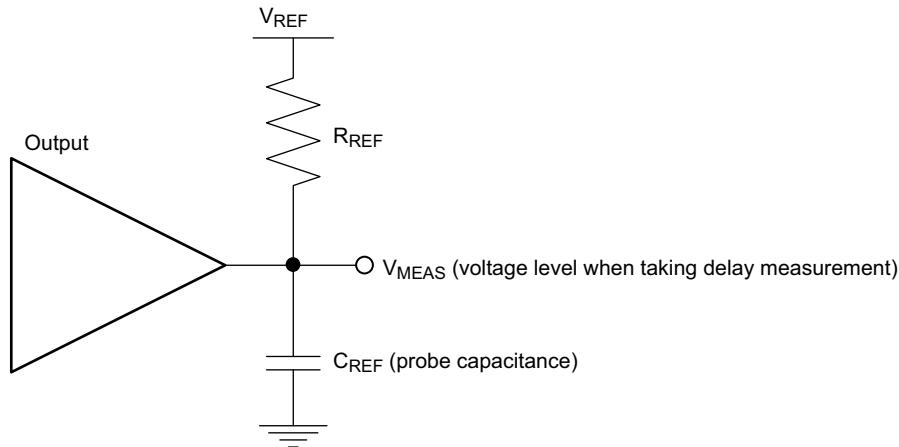
Table 77 specifies the values of T_{OUTBUF_DELAY_TE_PAD} and T_{INBUF_DELAY_IBUFDIS_O}. T_{OUTBUF_DELAY_TE_PAD} is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). T_{INBUF_DELAY_IBUFDIS_O} is the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than T_{OUTBUF_DELAY_TE_PAD} when the DCITERMDISABLE pin is used. In HD I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{OUTBUF_DELAY_TE_PAD} when the INTERMDISABLE pin is used.

Table 77: IOB 3-state Output Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V		0.85V		0.72V	
		-3	-2	-1	-2	-1	
T _{OUTBUF_DELAY_TE_PAD}	T input to pad high-impedance for HD I/O banks	6.318	6.318	6.369	6.318	6.369	ns
	T input to pad high-impedance for HP I/O banks	5.330	5.330	5.341	5.330	5.341	ns
T _{INBUF_DELAY_IBUFDIS_O}	IBUF turn-on time from IBUFDISABLE to O output for HD I/O banks	2.266	2.266	2.430	2.266	2.430	ns
	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	0.936	0.936	1.037	0.936	1.037	ns

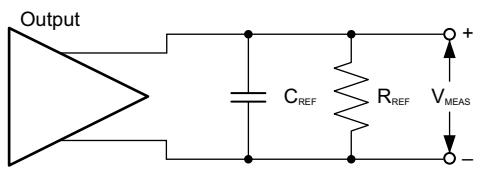
Output Delay Measurement Methodology

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in [Figure 1](#) and [Figure 2](#).



X16654-101316

Figure 1: Single-Ended Test Setup



X16640-101316

Figure 2: Differential Test Setup

Parameters V_{REF} , R_{REF} , C_{REF} , and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from [Table 79](#).
2. Record the time to V_{MEAS} .
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS} .
5. Compare the results of [step 2](#) and [step 4](#). The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Table 79: Output Delay Measurement Methodology

Description	I/O Standard Attribute	R _{REF} (Ω)	C _{REF} ⁽¹⁾ (pF)	V _{MEAS} (V)	V _{REF} (V)
LVC MOS, 1.2V	LVC MOS12	1M	0	0.6	0
LVC MOS, 1.5V	LVC MOS15	1M	0	0.75	0
LVC MOS, 1.8V	LVC MOS18	1M	0	0.9	0
LVC MOS, 2.5V	LVC MOS25	1M	0	1.25	0
LVC MOS, 3.3V	LVC MOS33	1M	0	1.65	0
LV TTL, 3.3V	LV TTL	1M	0	1.65	0
LVDCI, HSLVDCI, 1.5V	LVDCI_15, HSLVDCI_15	50	0	V _{REF}	0.75
LVDCI, HSLVDCI, 1.8V	LVDCI_15, HSLVDCI_18	50	0	V _{REF}	0.9
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	50	0	V _{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	50	0	V _{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	50	0	V _{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	50	0	V _{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	50	0	V _{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	50	0	V _{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	50	0	V _{REF}	0.75
SSTL18, class I and class II, 1.8V	SSTL18_I, SSTL18_II	50	0	V _{REF}	0.9
POD10, 1.0V	POD10	50	0	V _{REF}	1.0
POD12, 1.2V	POD12	50	0	V _{REF}	1.2
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	50	0	V _{REF}	0.6
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	50	0	V _{REF}	0.75
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	50	0	V _{REF}	0.9
DIFF_HSUL, 1.2V	DIFF_HSUL_12	50	0	V _{REF}	0.6
DIFF_SSTL12, 1.2V	DIFF_SSTL12	50	0	V _{REF}	0.6
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	50	0	V _{REF}	0.675
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	50	0	V _{REF}	0.75
DIFF_SSTL18, class I and II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	50	0	V _{REF}	0.9
DIFF_POD10, 1.0V	DIFF_POD10	50	0	V _{REF}	1.0
DIFF_POD12, 1.2V	DIFF_POD12	50	0	V _{REF}	1.2
LVDS (low-voltage differential signaling), 1.8V	LVDS	100	0	0 ⁽²⁾	0
SUB_LVDS, 1.8V	SUB_LVDS	100	0	0 ⁽²⁾	0
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	100	0	0 ⁽²⁾	0
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	1M	0	0.6	0

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. The value given is the differential output voltage.

Block RAM and FIFO Switching Characteristics

Table 80: Block RAM and FIFO Switching Characteristics

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units	
		0.90V	0.85V		0.72V			
		-3	-2	-1	-2	-1		
Maximum Frequency								
$F_{MAX_WF_NC}$	Block RAM (WRITE_FIRST and NO_CHANGE modes).	825	738	645	585	516	MHz	
F_{MAX_RF}	Block RAM (READ_FIRST mode).	718	637	575	510	460	MHz	
F_{MAX_FIFO}	FIFO in all modes without ECC.	825	738	645	585	516	MHz	
F_{MAX_ECC}	Block RAM and FIFO in ECC configuration without PIPELINE.	718	637	575	510	460	MHz	
	Block RAM and FIFO in ECC configuration with PIPELINE and Block RAM in WRITE_FIRST or NO_CHANGE mode.	825	738	645	585	516	MHz	
$T_{PW}^{(1)}$	Minimum pulse width.	495	542	543	577	578	ps	
Block RAM and FIFO Clock-to-Out Delays								
T_{RCKO_DO}	Clock CLK to DOUT output (without output register).	0.91	1.02	1.11	1.46	1.53	ns, Max	
$T_{RCKO_DO_REG}$	Clock CLK to DOUT output (with output register).	0.27	0.29	0.30	0.42	0.44	ns, Max	

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

Table 110: GTY Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics

Symbol	Description	All Speed Grades			Units
$F_{GTYDRPCLK}$	GTYDRPCLK maximum frequency.	250			MHz

Table 111: GTY Transceiver Reference Clock Switching Characteristics

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range.		60	—	820	MHz
T_{RCLK}	Reference clock rise time.	20% – 80%	—	200	—	ps
T_{FCLK}	Reference clock fall time.	80% – 20%	—	200	—	ps
T_{DCREF}	Reference clock duty cycle.	Transceiver PLL only	40	50	60	%

Table 112: GTY Transceiver Reference Clock Oscillator Selection Phase Noise Mask⁽¹⁾

Symbol	Description	Offset Frequency	Min	Typ	Max	Units
$QPLL_{REFCLKMASK}$	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 156.25 MHz.	10 kHz	—	—	-112	dBc/Hz
		100 kHz	—	—	-128	
		1 MHz	—	—	-145	
	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	—	—	-103	dBc/Hz
		100 kHz	—	—	-123	
		1 MHz	—	—	-143	
	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 625 MHz.	10 kHz	—	—	-98	dBc/Hz
		100 kHz	—	—	-117	
		1 MHz	—	—	-140	
$CPLL_{REFCLKMASK}$	CPLL reference clock select phase noise mask at REFCLK frequency = 156.25 MHz.	10 kHz	—	—	-112	dBc/Hz
		100 kHz	—	—	-128	
		1 MHz	—	—	-145	
		50 MHz	—	—	-145	
	CPLL reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	—	—	-103	dBc/Hz
		100 kHz	—	—	-123	
		1 MHz	—	—	-143	
		50 MHz	—	—	-145	
	CPLL reference clock select phase noise mask at REFCLK frequency = 625 MHz.	10 kHz	—	—	-98	dBc/Hz
		100 kHz	—	—	-117	
		1 MHz	—	—	-140	
		50 MHz	—	—	-144	

Notes:

- For reference clock frequencies not in this table, use the phase-noise mask for the nearest reference clock frequency.
- This reference clock phase-noise mask is superseded by any reference clock phase-noise mask that is specified in a supported protocol, e.g., PCIe.

Integrated Interface Block for Interlaken

More information and documentation on solutions using the integrated interface block for Interlaken can be found at [UltraScale+ Interlaken](#). The *UltraScale Architecture and Product Overview* ([DS890](#)) lists how many blocks are in each Zynq UltraScale+ MPSoC. This section describes the following Interlaken configurations.

- 12 x 12.5 Gb/s protocol and lane logic mode ([Table 118](#)).
- 6 x 25.78125 Gb/s and 6 x 28.21 Gb/s protocol and lane logic mode ([Table 119](#)).
- 12 x 25.78125 Gb/s lane logic only mode ([Table 120](#)).

Zynq UltraScale+ MPSoCs in the SFVB784, FFVA676, and FFVA1156 packages are only supported using the 12 x 12.5 Gb/s Interlaken configuration. See [Table 109](#) for the F_{GTYMAX} description.

Table 118: Maximum Performance for Interlaken 12 x 12.5 Gb/s Protocol and Lane Logic Mode Designs

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages						Units
		0.90V		0.85V		0.72V		
		-3	-2	-1	-2	-1		
$F_{RX_SERDES_CLK}$	Receive serializer/deserializer clock	195.32	195.32	195.32	195.32	195.32	195.32	MHz
$F_{TX_SERDES_CLK}$	Transmit serializer/deserializer clock	195.32	195.32	195.32	195.32	195.32	195.32	MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00	250.00	250.00	250.00	250.00	250.00	MHz
		Min ⁽¹⁾	Max	Min ⁽¹⁾	Max	Min ⁽¹⁾	Max	Min ⁽¹⁾
F_{CORE_CLK}	Interlaken core clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00
F_{LBUS_CLK}	Interlaken local bus clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00

Notes:

1. These are the minimum clock frequencies at the maximum lane performance.

Table 124: PL SYSMON Specifications (Cont'd)

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
On-Chip Sensor Accuracy						
Temperature sensor error ⁽¹⁾⁽³⁾		T _j = -55°C to 125°C (with external REF)	-	-	±3	°C
		T _j = -55°C to 110°C (with internal REF)	-	-	±3.5	°C
		T _j = 110°C to 125°C (with internal REF)	-	-	±5	°C
Supply sensor error ⁽⁴⁾		Supply voltages 0.72V to 1.2V, T _j = -40°C to 100°C (with external REF)	-	-	±0.5	%
		Supply voltages 0.72V to 1.2V, T _j = -55°C to 125°C (with external REF)	-	-	±1.0	%
		All other supply voltages, T _j = -40°C to 100°C (with external REF)	-	-	±1.0	%
		All other supply voltages, T _j = -55°C to 125°C (with external REF)	-	-	±2.0	%
		Supply voltages 0.72V to 1.2V, T _j = -40°C to 100°C (with internal REF)	-	-	±1.0	%
		Supply voltages 0.72V to 1.2V, T _j = -55°C to 125°C (with internal REF)	-	-	±2.0	%
		All other supply voltages, T _j = -40°C to 100°C (with internal REF)	-	-	±1.5	%
		All other supply voltages, T _j = -55°C to 125°C (with internal REF)	-	-	±2.5	%
Conversion Rate⁽⁵⁾						
Conversion time—continuous	t _{CONV}	Number of ADCCLK cycles	26	-	32	Cycles
Conversion time—event	t _{CONV}	Number of ADCCLK cycles	-	-	21	Cycles
DRP clock frequency	DCLK	DRP clock frequency	8	-	250	MHz
ADC clock frequency	ADCCLK	Derived from DCLK	1	-	5.2	MHz
DCLK duty cycle			40	-	60	%
SYSMON Reference⁽⁶⁾						
External reference	V _{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
On-chip reference		Ground V _{REFP} pin to AGND, T _j = -40°C to 100°C	1.2375	1.25	1.2625	V
		Ground V _{REFP} pin to AGND, T _j = -55°C to 125°C	1.225	1.25	1.275	V

Notes:

1. ADC offset errors are removed by enabling the ADC automatic offset calibration feature. The values are specified for when this feature is enabled.
2. See the *Analog Input* section in the *UltraScale Architecture System Monitor User Guide* ([UG580](#)).
3. When reading temperature values directly from the PMBus interface, the SYSMON has a +4°C offset due to the transfer function used by the PMBus application. For example, the external REF temperature sensor error's range of ±3°C becomes +1°C to +7°C when the temperature is read through the PMBus interface.
4. Supply sensor offset and gain errors are removed by enabling the automatic offset and gain calibration feature. The values are specified for when this feature is enabled.
5. See the *Adjusting the Acquisition Settling Time* section in the *UltraScale Architecture System Monitor User Guide* ([UG580](#)).
6. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted.

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